

ON Semiconductor

Is Now

onsemi™

To learn more about onsemi™, please visit our website at
www.onsemi.com

onsemi and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.



ON Semiconductor®

FDA16N50-F109

N-Channel UniFET™ MOSFET

500V, 16.5 A, 380 mΩ

Features

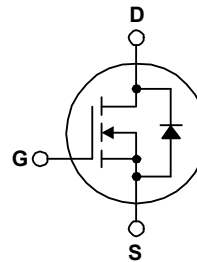
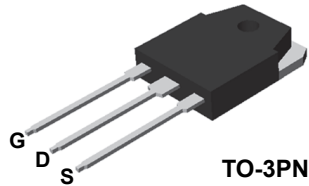
- $R_{DS(on)} = 380\text{ m}\Omega$ (Max.) @ $V_{GS} = 10$, $I_D = 8.3\text{ A}$
- Low Gate Charge (Typ. 32 nC)
- Low C_{rSS} (Typ. 20 pF)
- 100% Avalanche Tested

Applications

- PDP TV
- Uninterruptible Power Supply

Description

UniFET™ MOSFET is ON Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter		FDA16N50-F109	Unit
V_{DSS}	Drain-Source Voltage		500	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	16.5	A
		- Continuous ($T_C = 100^\circ\text{C}$)	9.9	A
I_{DM}	Drain Current	- Pulsed (Note 1)	66	A
V_{GSS}	Gate-Source voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	780	mJ
I_{AR}	Avalanche Current	(Note 1)	16.5	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	20.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	205	W
		- Derate above 25°C	2.1	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FDA16N50-F109	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.6	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	

FDA16N50-F109 — N-Channel UniFET™ MOSFET

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA16N50	FDA16N50-F109	TO-3PN	Tube	N/A	30 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to 25°C	--	0.5	--	$V/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_C = 125^\circ\text{C}$	--	--	1 10	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30V, V_{DS} = 0V$	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 8.3A$	--	0.31	0.38	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40V, I_D = 8.3A$	--	23	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$	--	1495	1945	pF
C_{oss}	Output Capacitance		--	235	310	pF
C_{rss}	Reverse Transfer Capacitance		--	20	30	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250V, I_D = 16A$ $R_G = 25\Omega$	--	40	90	ns
t_r	Turn-On Rise Time		--	150	310	ns
$t_{d(off)}$	Turn-Off Delay Time		--	65	140	ns
t_f	Turn-Off Fall Time		(Note 4)	--	80	170
Q_g	Total Gate Charge	$V_{DS} = 400V, I_D = 16A$ $V_{GS} = 10V$	--	32	45	nC
Q_{gs}	Gate-Source Charge		--	8.5	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	14	--
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	9.2	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	37	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 16.5A$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0V, I_S = 16A$ $di_F/dt = 100A/\mu s$	--	490	--	ns
Q_{rr}	Reverse Recovery Charge		--	5.0	--	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 5.1\text{mH}, I_{AS} = 16.5A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 16.5A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Characteristics

Figure 1. On-Region Characteristics

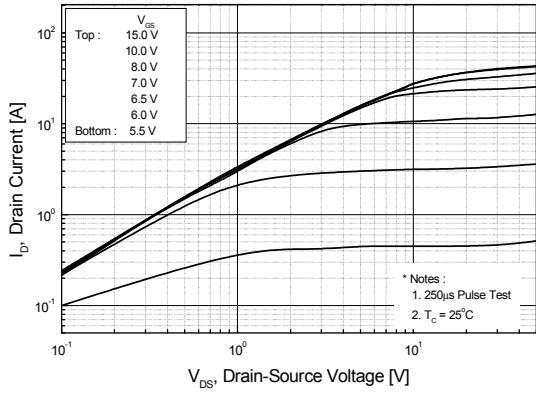


Figure 2. Transfer Characteristics

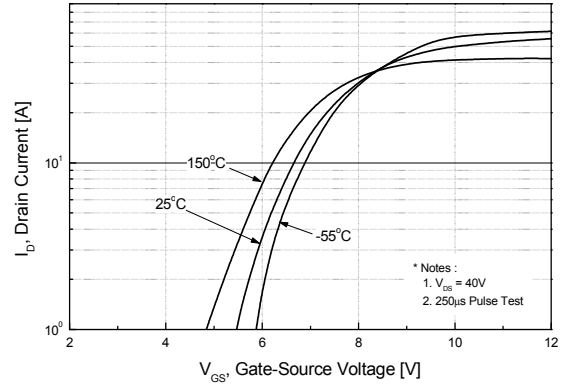


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

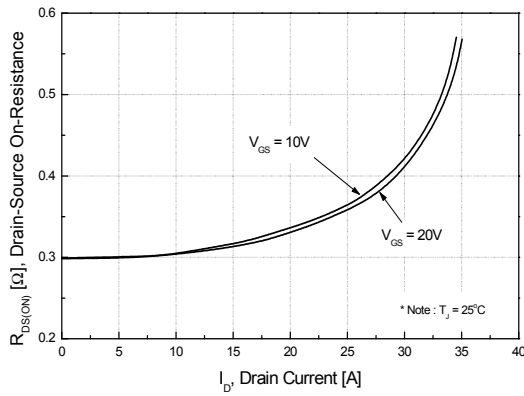


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

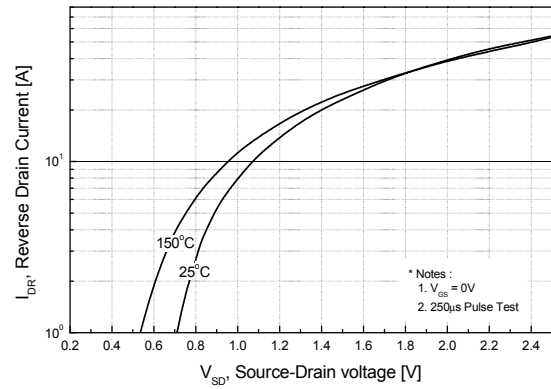


Figure 5. Capacitance Characteristics

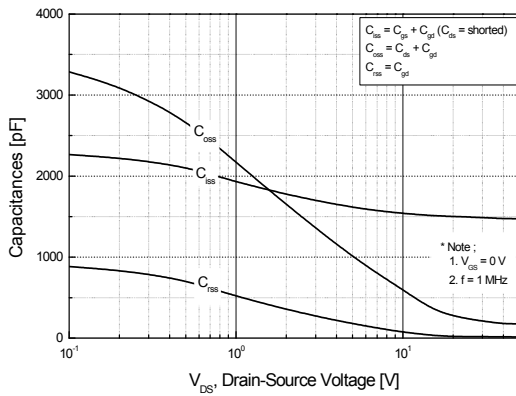
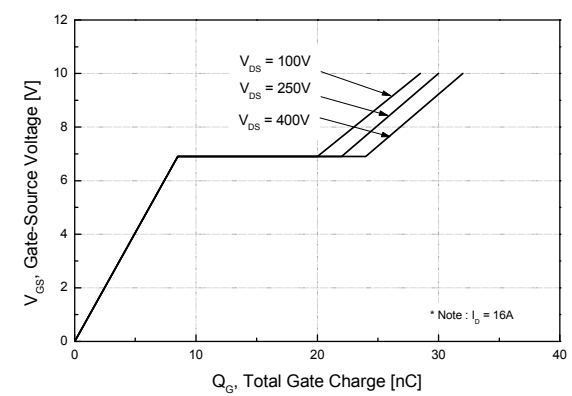


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

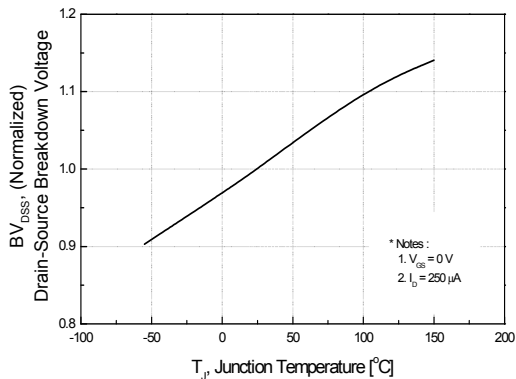


Figure 8. On-Resistance Variation vs. Temperature

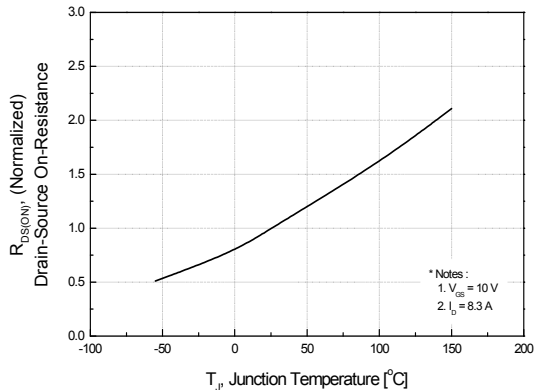


Figure 9. Maximum Safe Operating Area

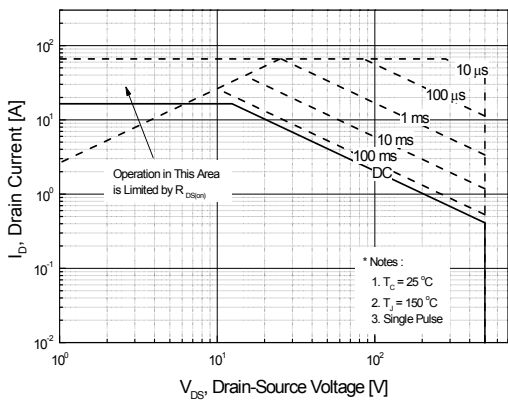


Figure 10. Maximum Drain Current vs. Case Temperature

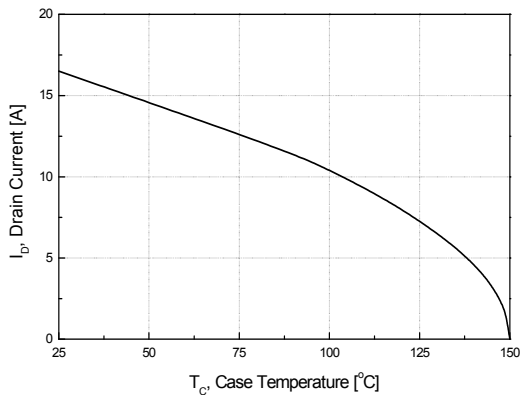


Figure 11. Transient Thermal Response Curve

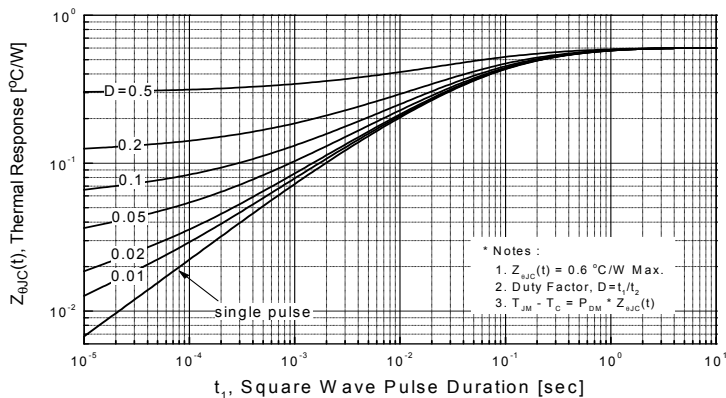


Figure 12. Gate Charge Test Circuit & Waveform

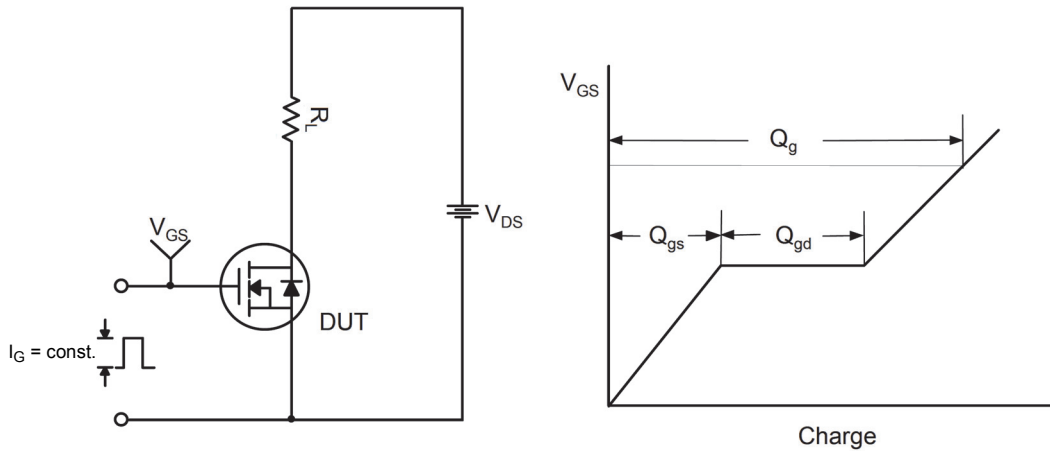


Figure 13. Resistive Switching Test Circuit & Waveforms

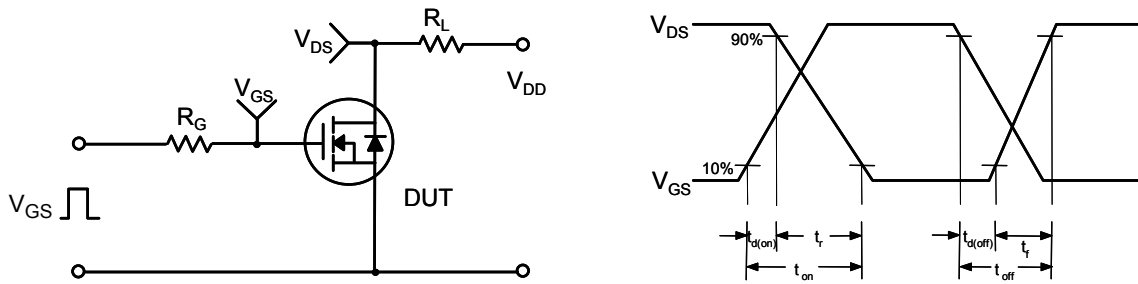


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

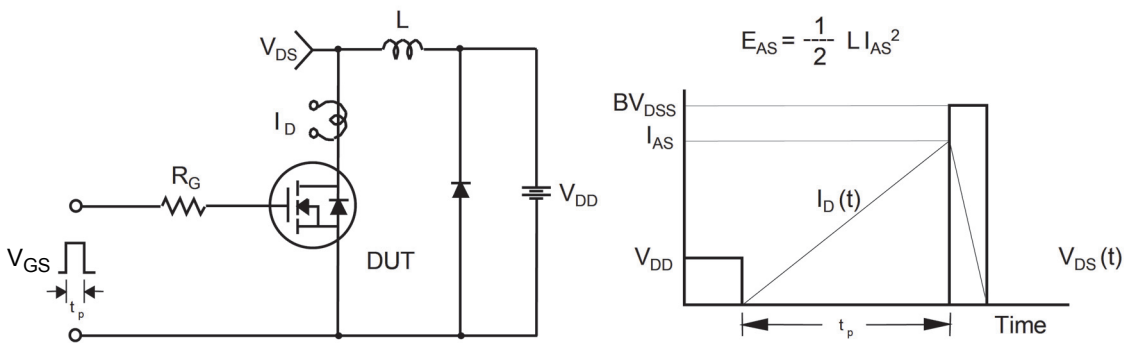
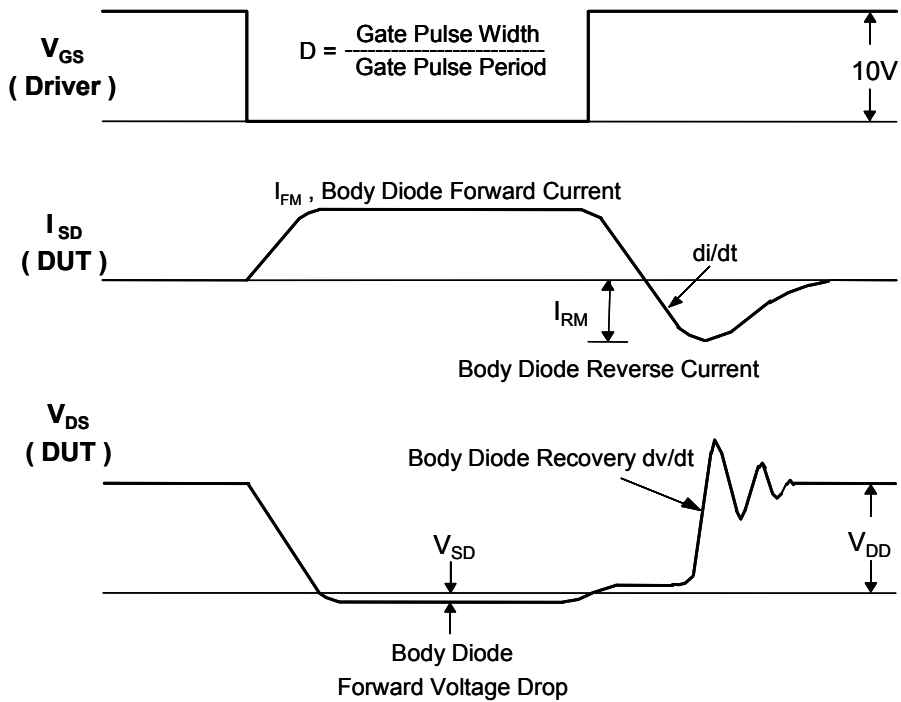
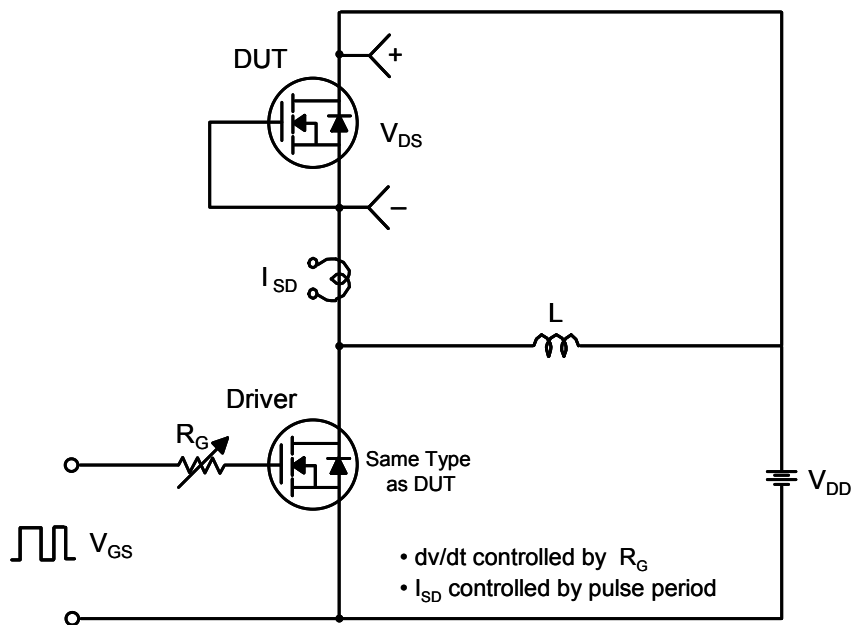
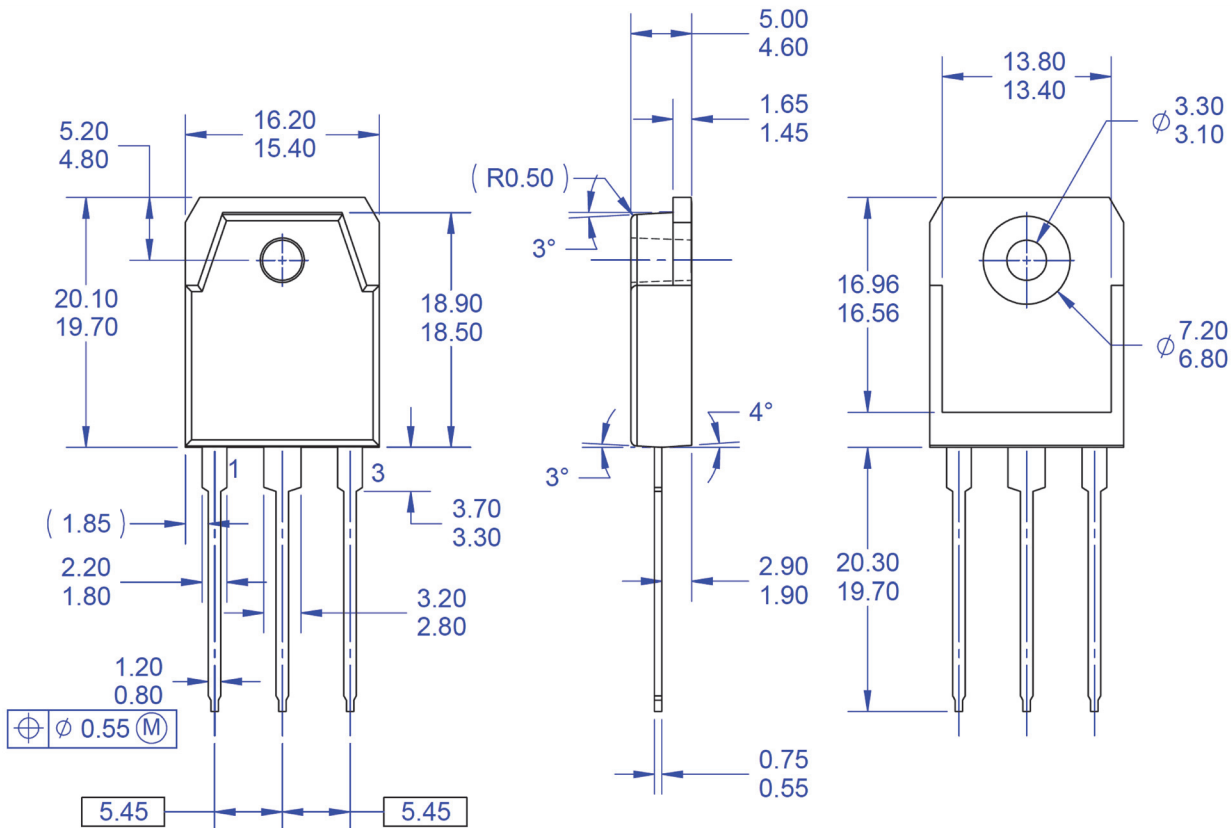


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5-2009.
- DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

Package drawings are provided as a service to customers considering ON Semiconductor components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a ON Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of ON Semiconductor's worldwide terms and conditions, specifically the warranty therein, which covers ON Semiconductor products.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local
Sales Representative